MMBT4401LT1

Preferred Device

Switching Transistor

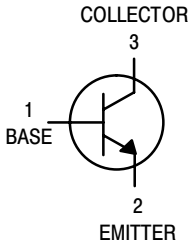
NPN Silicon

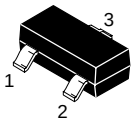
ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Packages are Available





SOT−23 (TO−236)
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	40	Vdc
Collector−Base Voltage	V_{CBO}	60	Vdc
Emitter−Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	600	mAdc

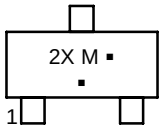
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) @T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

MARKING DIAGRAM



2X = Specific Device Code
M = Date Code*
▪ = Pb−Free Package
(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT4401LT1	SOT−23	3000 Tape & Reel
MMBT4401LT1G	SOT−23 (Pb−Free)	3000 Tape & Reel
MMBT4401LT3	SOT−23	10,000 Tape & Reel
MMBT4401LT3G	SOT−23 (Pb−Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

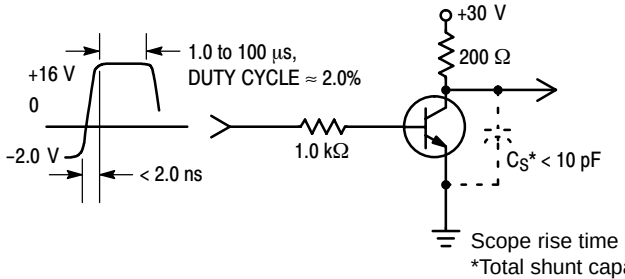
Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (Note 3)	(I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	−	Vdc
Collector−Base Breakdown Voltage	(I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	−	Vdc
Emitter−Base Breakdown Voltage	(I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	−	Vdc
Base Cutoff Current	(V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{BEV}	−	0.1	μAdc
Collector Cutoff Current	(V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{CEX}	−	0.1	μAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain		h_{FE}			−
	(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)		20	−	
	(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)		40	−	
	(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		80	−	
	(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)		100	300	
	(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)		40	−	
Collector−Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
	(I_C = 150 mAdc, I_B = 15 mAdc)		−	0.4	
	(I_C = 500 mAdc, I_B = 50 mAdc)		−	0.75	
Base−Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
	(I_C = 150 mAdc, I_B = 15 mAdc)		0.75	0.95	
	(I_C = 500 mAdc, I_B = 50 mAdc)		−	1.2	
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product	(I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	250	−	MHz
Collector−Base Capacitance	(V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	−	6.5	pF
Emitter−Base Capacitance	(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{eb}	−	30	pF
Input Impedance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	1.0	15	kΩ
Voltage Feedback Ratio	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	0.1	8.0	X 10^{-4}
Small−Signal Current Gain	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	40	500	−
Output Admittance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	1.0	30	μmhos
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, V_{EB} = 2.0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	−	15	ns
Rise Time		t_r	−	20	
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	−	225	ns
Fall Time		t_f	−	30	

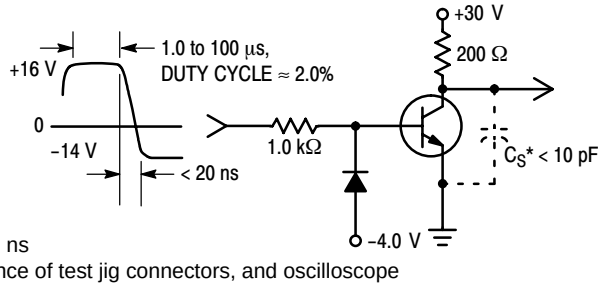
3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS



Scope rise time < 4.0 ns

Figure 1. Turn−On Time



*Total shunt capacitance of test jig connectors, and oscilloscope

Figure 2. Turn−Off Time

TRANSIENT CHARACTERISTICS

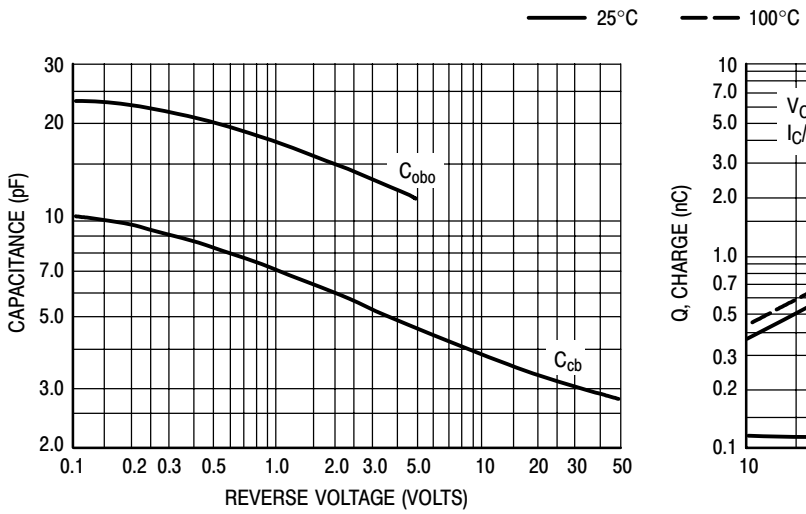


Figure 3. Capacitances

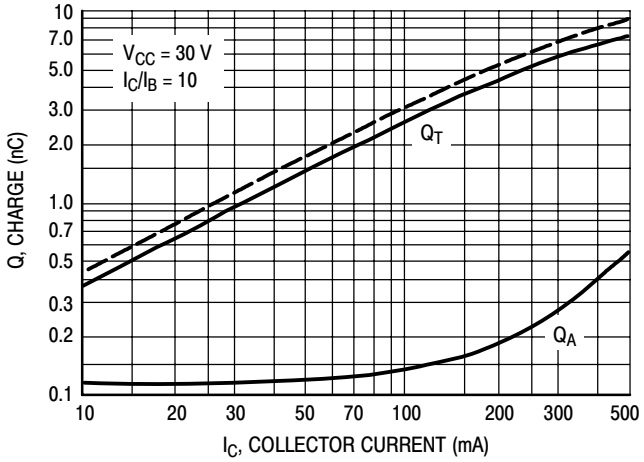


Figure 4. Charge Data

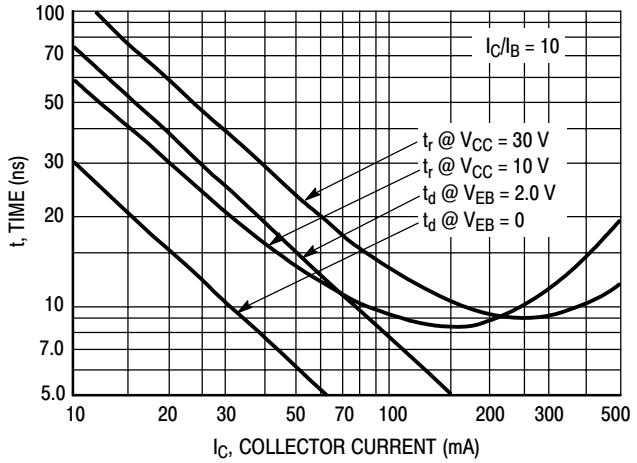


Figure 5. Turn−On Time

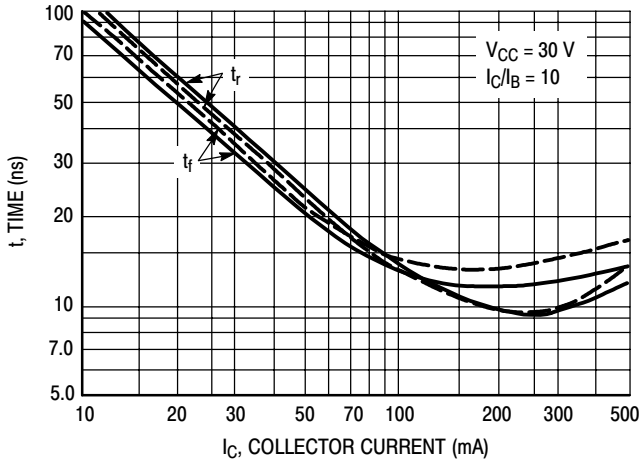


Figure 6. Rise and Fall Times

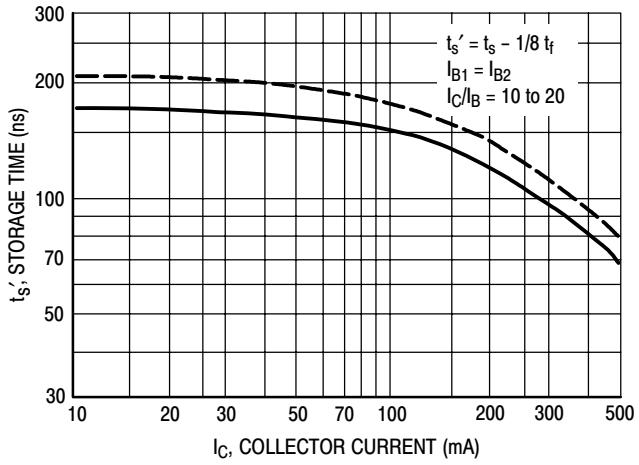


Figure 7. Storage Time

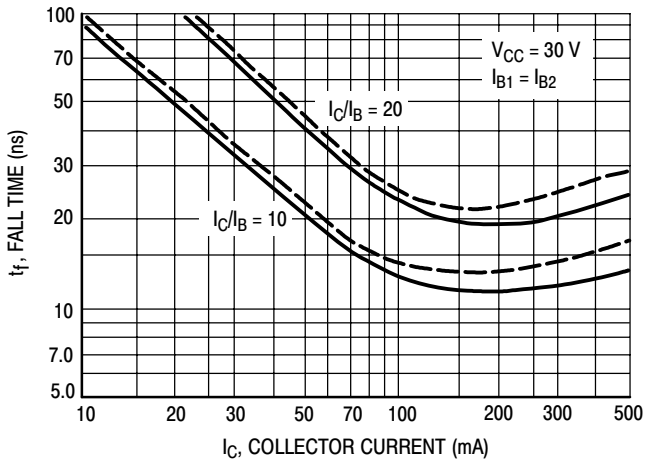


Figure 8. Fall Time

SMALL−SIGNAL CHARACTERISTICS NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C; Bandwidth = 1.0 Hz

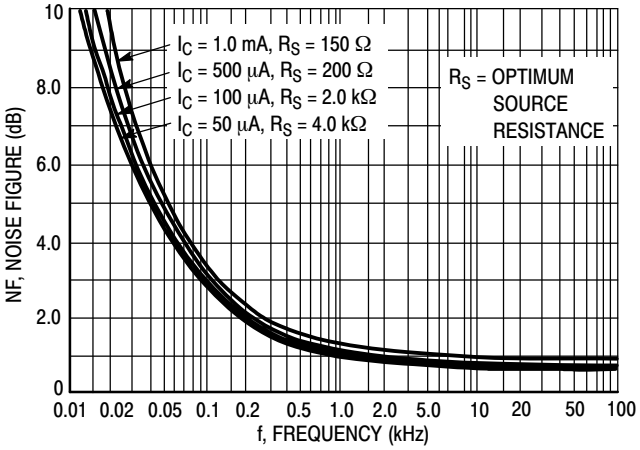


Figure 9. Frequency Effects

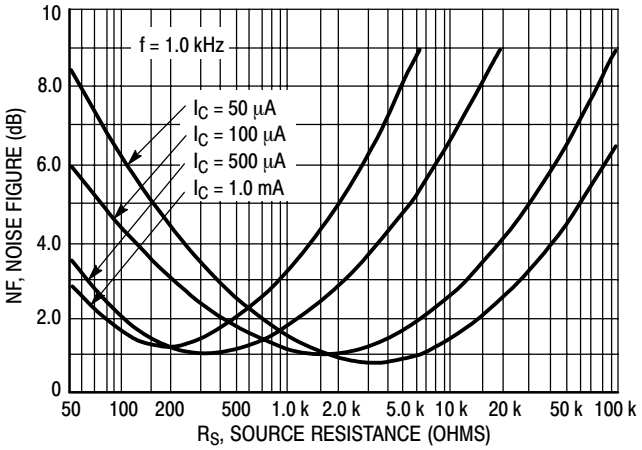


Figure 10. Source Resistance Effects

h PARAMETERS

V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high−gain and a low−gain unit were selected from the MMBT4401LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

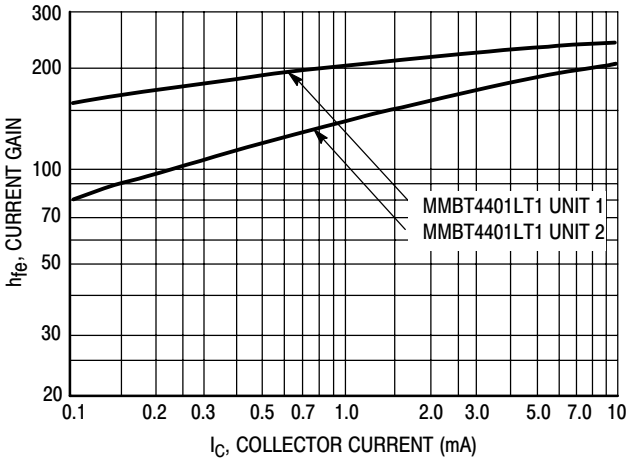


Figure 11. Current Gain

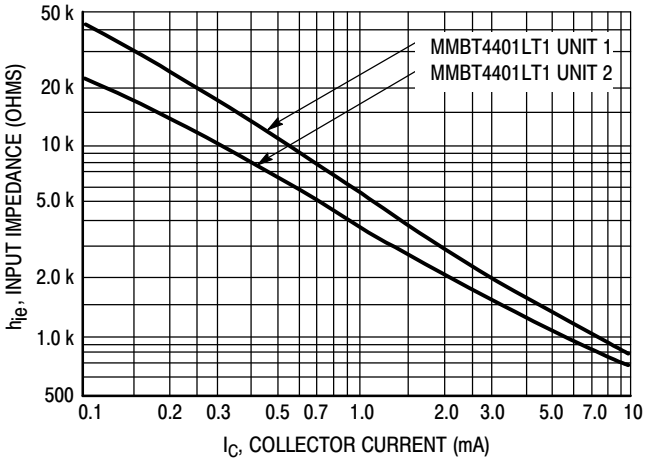


Figure 12. Input Impedance

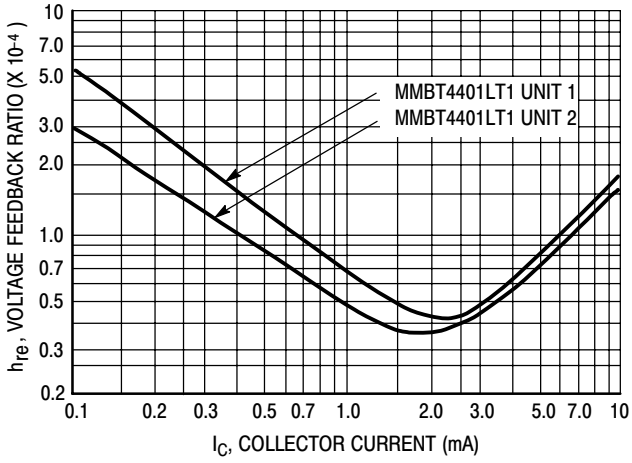


Figure 13. Voltage Feedback Ratio

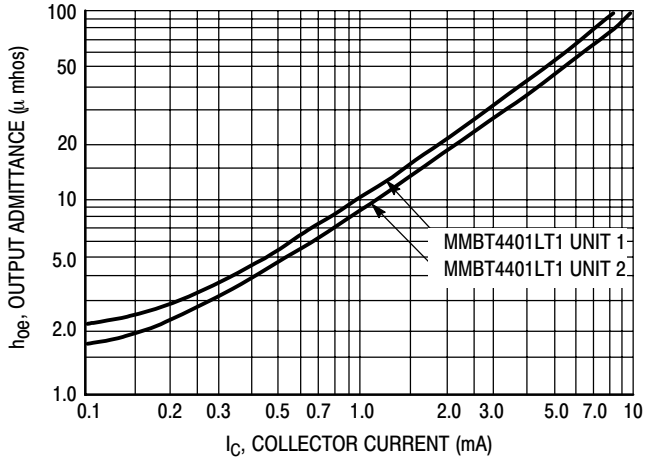


Figure 14. Output Admittance

STATIC CHARACTERISTICS

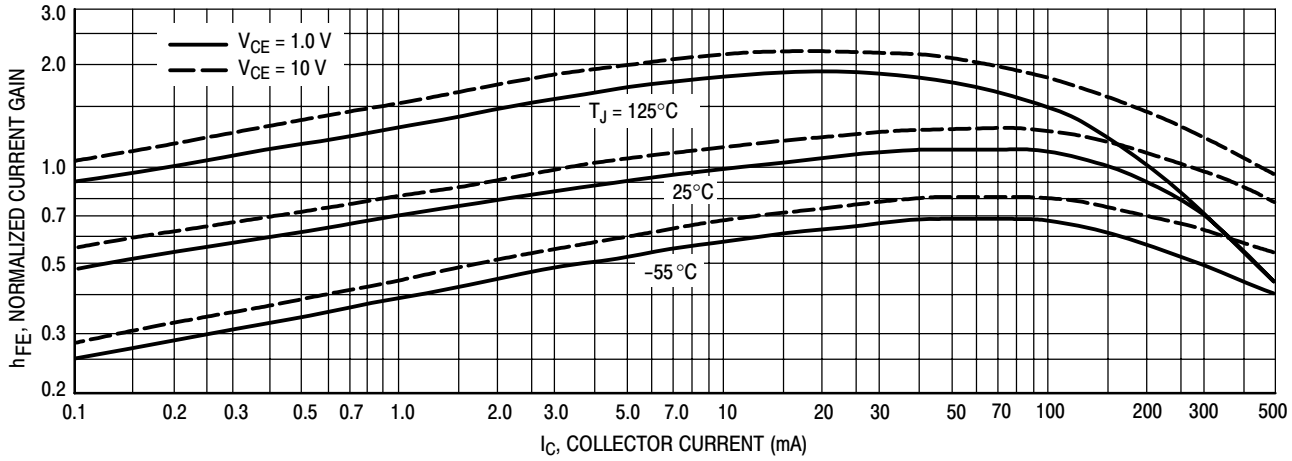


Figure 15. DC Current Gain

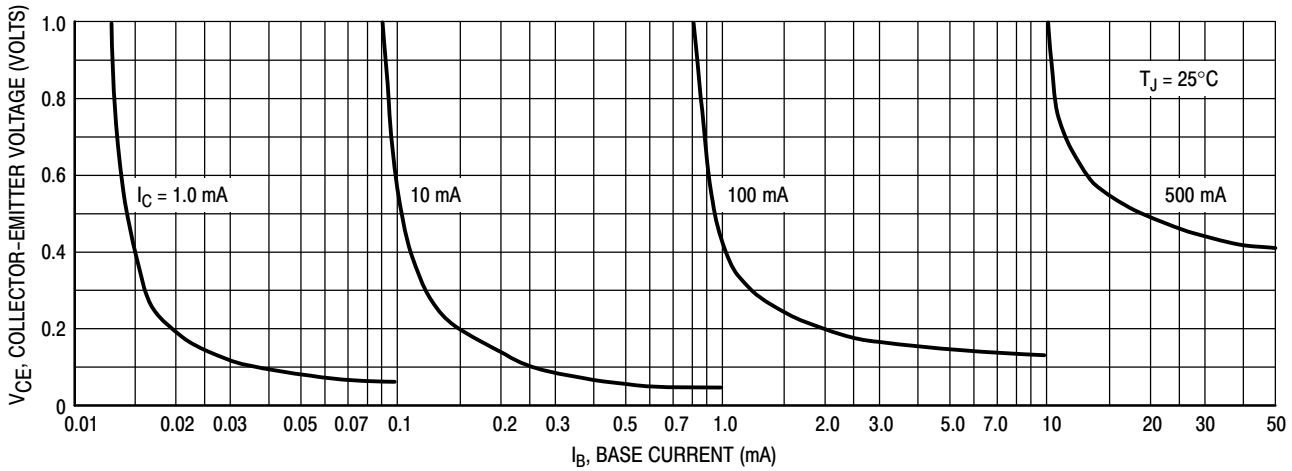


Figure 16. Collector Saturation Region

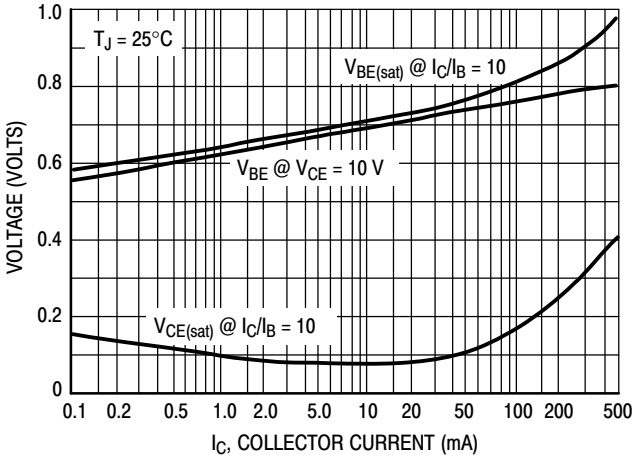


Figure 17. “On” Voltages

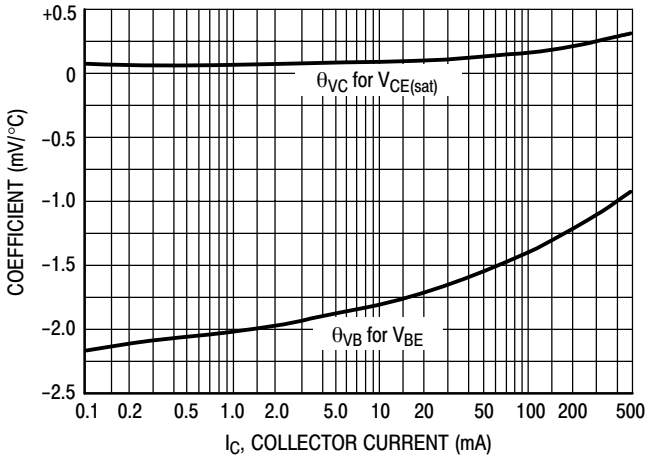
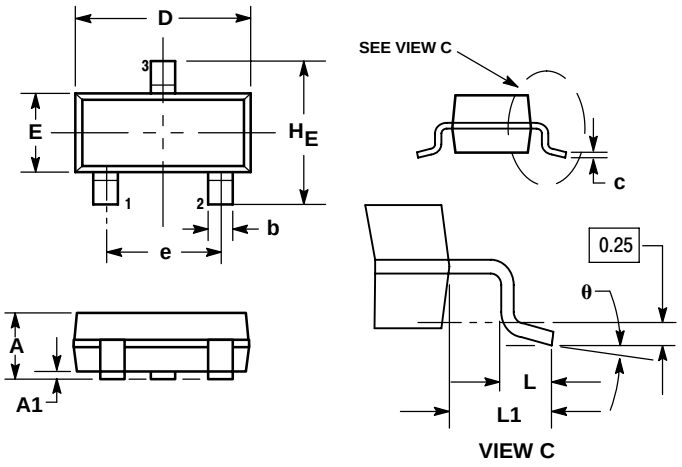


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AN

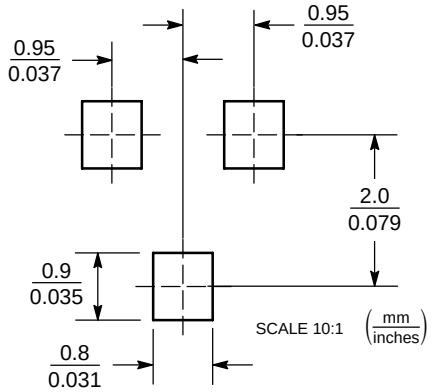


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01 THRU −07 AND −09 OBSOLETE, NEW STANDARD 318−08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.